

NS8AT - NS8MT

Glass Passivated General Purpose

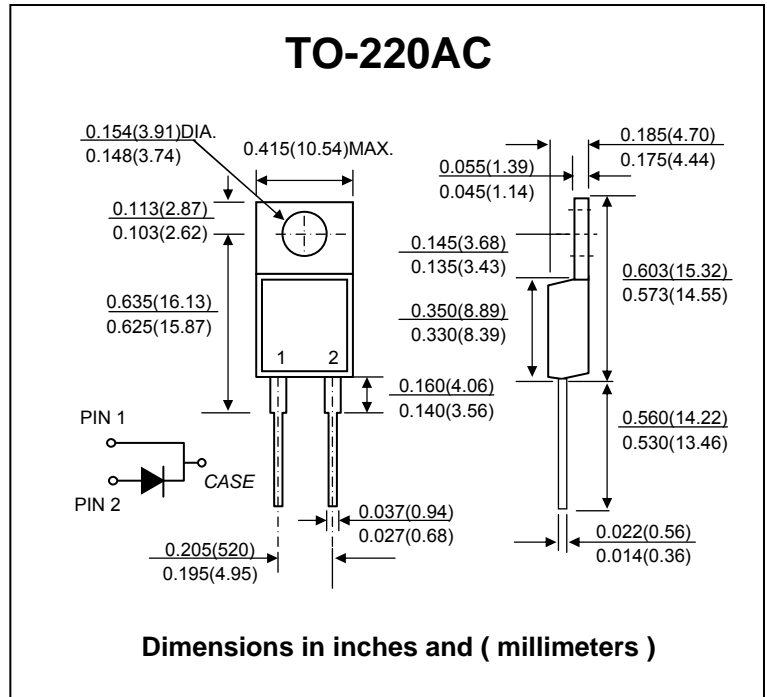
PRV : 50 - 1000 Volts
Io : 8.0 Ampere

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Glass passivated chip junction
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : Epoxy, Molded
- * Lead Temperature for Soldering Purposes:
260°C Max. for 10 Seconds
- * Polarity: As marked
- * Mounting Position: Any
- * Weight : 2.24 grams (Approximately)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	NS8 AT	NS8 BT	NS8 DT	NS8 GT	NS8 JT	NS8 KT	NS8 MT	UNIT	
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V	
Maximum Working Reverse Voltage	V_{RWM}	35	70	140	280	420	560	700	V	
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V	
Maximum Average Forward Current, $T_c = 100^\circ\text{C}$	$I_{F(AV)}$	8.0								A
Maximum Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	125								A
Maximum Instantaneous Forward Voltage at $I_F = 8\text{ A}$	V_F	1.1								V
Maximum Reverse Current at $T_c = 25^\circ\text{C}$	I_R	10								μA
Rated DC Blocking Voltage $T_c = 100^\circ\text{C}$	$I_{R(H)}$	100								μA
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0								$^\circ\text{C/W}$
Junction Temperature Range	T_J	- 55 to + 150								$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 55 to + 150								$^\circ\text{C}$

RATING AND CHARACTERISTIC CURVES (NS8AT ~ NS8MT)

FIG.1 - FORWARD CURRENT DERATING CURRENT

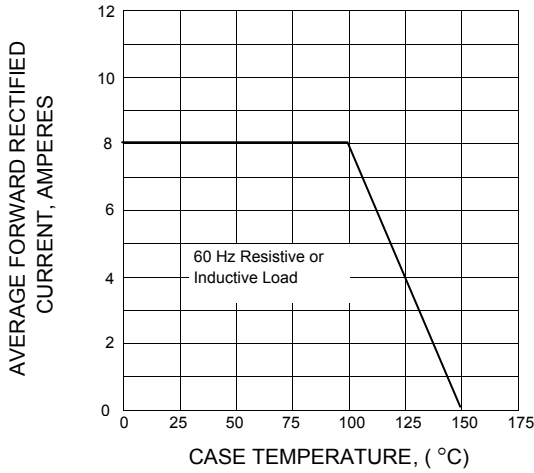


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

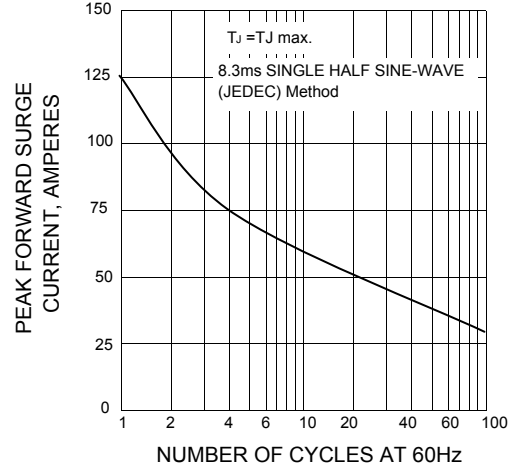


FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

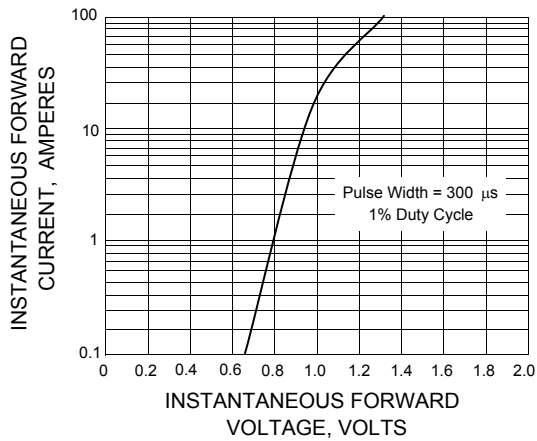


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

